VUSG002R26ANA

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
20V	260mΩ@4.5V	0.75A
	360mΩ@2.5V	
	590mΩ@1.8V	

Symbol

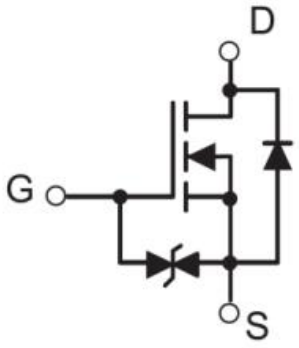
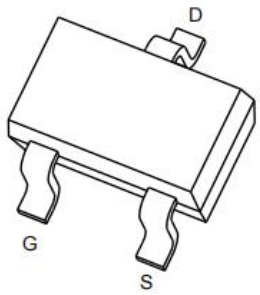


Figure 1 Symbol of VUSG002R26ANA

Features

- Excellent $R_{DS(on)}$ and Low Gate Charge
- Trench FET Power MOSFET
- ESD Protected

Package Type



SOT-323

Figure 2 Package Type of VUSG002R26ANA

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Small Portable Electronics
- Level shift

Ordering Information

Product Name	Package
VUSG002R26ANA	SOT-323

Absolute Maximum Ratings (T_A= 25 ºC, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±12	V
Continuous Drain Current	I_D	0.75	A
Pulsed Drain Current[Note1]	I_{DM}	3	A
Total Power Dissipation[Note2]	P_D	0.2	W
Junction Temperature	T_J	150	ºC
Storage Temperature	T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient[Note1]	$R_{\theta JA}$		819		ºC/W

Electrical Characteristics (T_A= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 20V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±10V, V_{DS}= 0V			±20	uA
Gate Threshold Voltage[Note3]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	0.35	0.75	1.1	V
Drain-source on-resistance[Note3]	$R_{DS(on)}$	V_{GS}= 4.5V, I_D= 0.65A		190	260	
		V_{GS}= 2.5V, I_D= 0.55A		260	360	
		V_{GS}= 1.8V, I_D= 0.45A		390	590	
Forward tranconductance[Note3]	g_{FS}	V_{DS}= 10V, I_D= 0.8A		1.6		S
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=16V		79	120	pF
Output Capacitance	C_{OSS}	V_{GS}=0V		13	20	pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		9	15	pF
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 10V		6.7		ns
Turn-on Rise Time	t_r	V_{GEN}=4.5V		4.8		
Turn-off Delay Time	$t_{d(off)}$	I_D= 0.5A		17.3		
Turn-off Fall Time	t_f	R_{GEN}=10Ω		7.4		
Diode Characteristics						
Diode Forward Voltage [Note3]	V_{SD}	V_{GS}=0V, I_S= 0.15A			1.2	V

Notes :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at T_A=25C.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 3: Transfer Characteristics

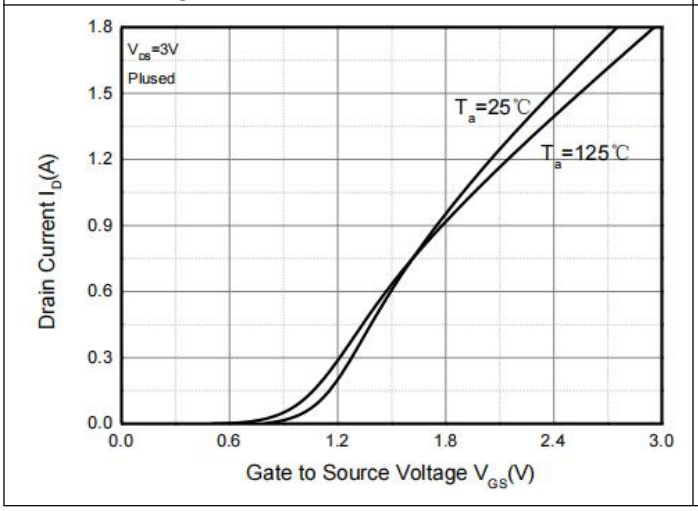


Figure 4: Output Characteristics

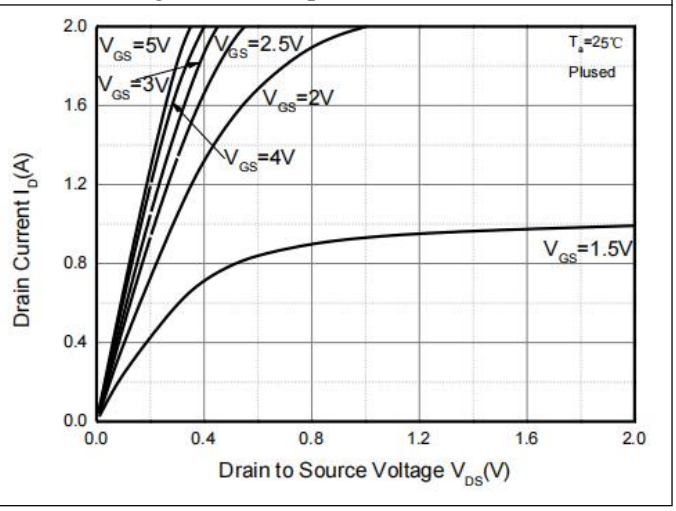


Figure 5: On-Resistance vs. Drain Current

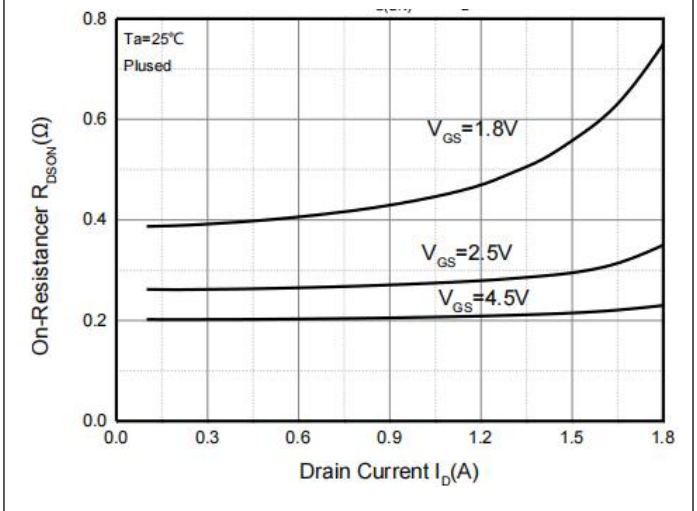


Figure 6: On-Resistance vs. Gate Voltage

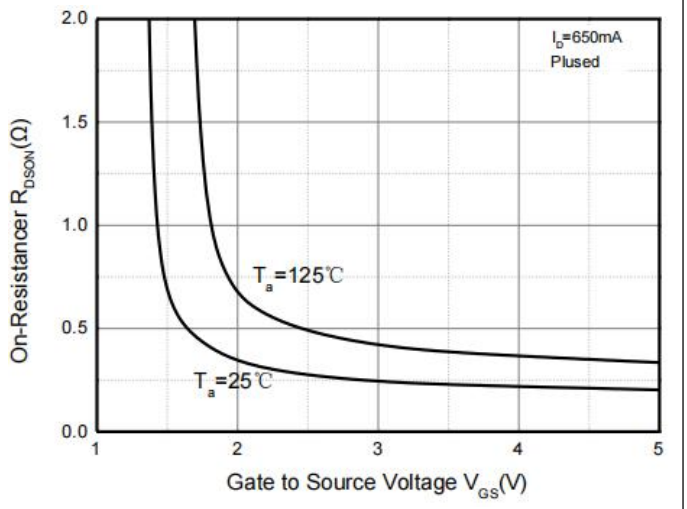


Figure 7: Body Diode Characteristics

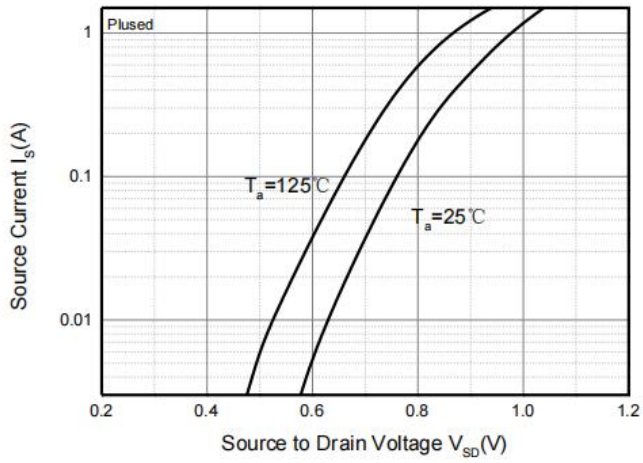
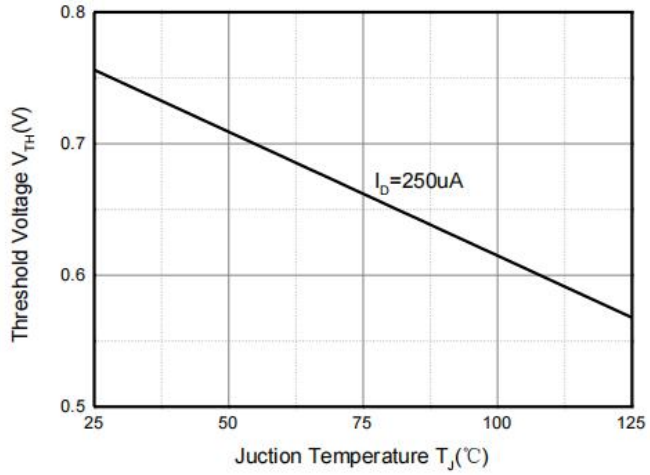
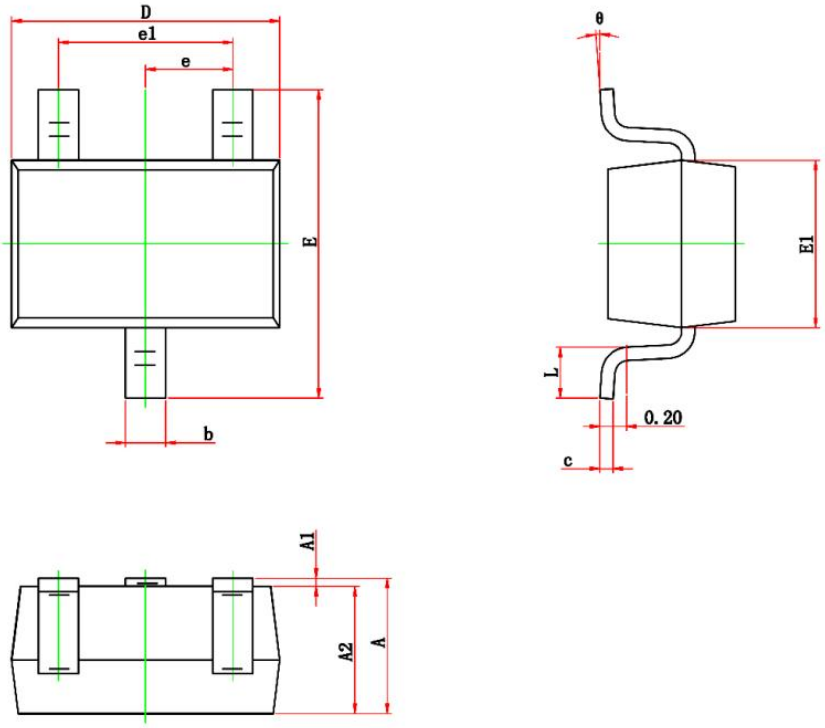


Figure 8: Threshold Voltage



Mechanical Dimensions:

SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.050	0.150	0.002	0.006
D	1.900	2.200	0.075	0.087
E	2.000	2.450	0.079	0.096
E1	1.150	1.350	0.045	0.053
e	0.650TYP.		0.026TYP.	
e1	1.200	1.400	0.047	0.055
L	0.200	0.460	0.008	0.018
θ	0°	8°	0°	8°

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